Semi-Invasive Attacks

Sample Preparation

Decapsulation

Imaging

Backside imaging techniques

Perform the Attacks

UV light attacks

Active photon probing

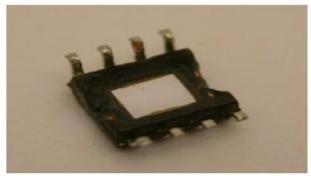
Optical Fault injection attacks

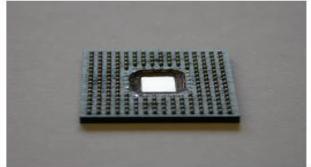
28 October 2024 1

Semi-Invasive Attacks: Sample Preparation

- Decapsulation of the chip to prepare it for attacks.
- For the modern chips, backside decapsulation is used
 - There is no need to use chemicals







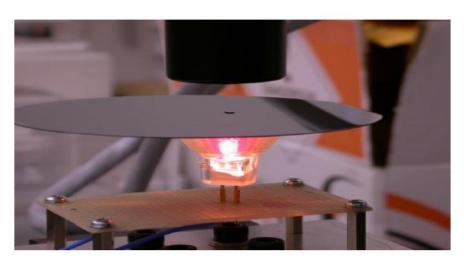
28 October 2024

Semi-Invasive Attacks: Imaging

- Down to 0.8 µm technology, it was possible to identify all the major elements of microcontrollers – ROM, EEPROM, SRAM, CPU
- Difficult to distinguish for newer technologies
- Can be observed with infrared light from rear side
- Backside imaging also is useful to extract the Mask ROM content

28 October 2024 3

Semi-Invasive Attacks: Imaging



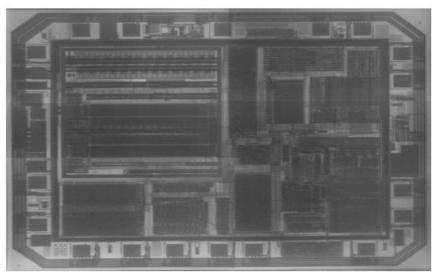
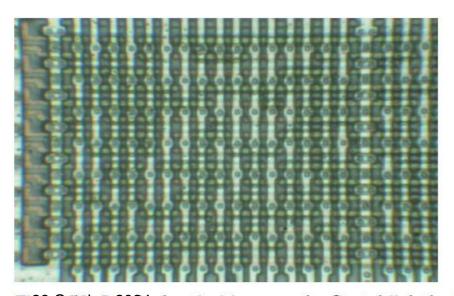


Figure 78. Transmitted light setup and image of the MSP430F112 microcontroller. 50x magnification



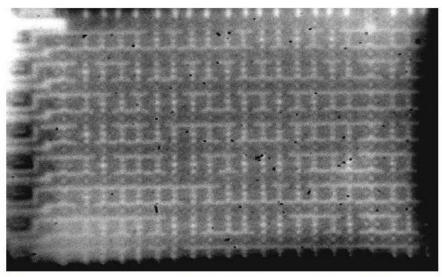


Fig8r@ct9best2024rd optical image and reflected light backside image of the Mask ROM inside MC68HC705P6A microcontroller built with 1.0 μm technology. 500× magnification

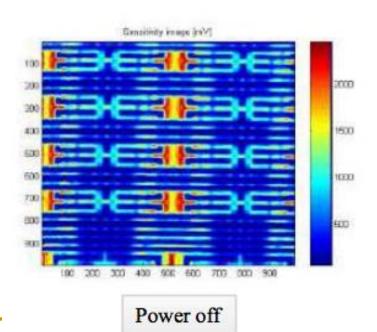
Reading the Logic State of CMOS Transistors

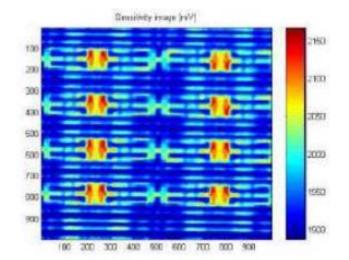
Red low power laser beams ionize active areas

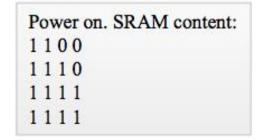
Power off imaging identifies active areas

Power on imaging distinguishes between closed and

opened transistor channels







Semi-Invasive: Optical Fault Injection Attacks

 Illumination of a target transistor causes it to conduct, thereby inducing a transient fault

- Such attacks
 - Practical
 - Do not require expensive laser equipment
 - Any individual bit of SRAM in microcontroller can be set or reset

28 October 2024 6

Fault injection attacks: Changing SRAM contents

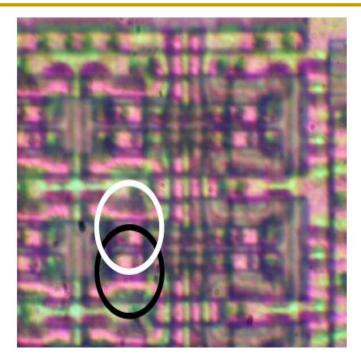
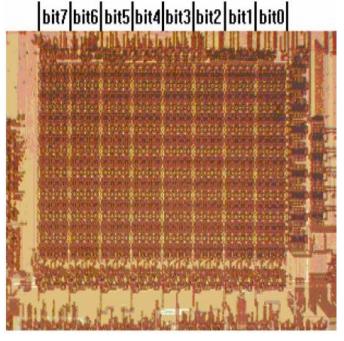


Figure 91. SRAM memory array with maximum Figure 92. Allocation of data bits in SRAM memory magnification (1500x)



array

- Focusing the light spot from the lamp on the area shown by the white circle caused the cell to change its state from '1' to '0', with no change if the state was already '0'.
- By focusing the spot on the area shown by the black circle, the cell changed its state from '0' to '1' or remained in state '1'.

28 October 2024 7

Non-volatile memory contents modification

- EPROM, EEPROM and Flash memory cells are even more sensitive to fault injection attacks.
- They can be changed by light
- This attacks can be used to disable security fuses
 - The light should be focused down to the security fuse
- These attacks do not work on modern chips built in smaller sizes

28 October 2024